

HIGH FREQUENCY LOW NOISE AMPLIFIER  
NPN SILICON EPITAXIAL TRANSISTOR  
SUPER MINI MOLD**DESCRIPTION**

The 2SC4227 is a low supply voltage transistor designed for VHF, UHF low noise amplifier.

It is suitable for a high density surface mount assembly since the transistor has been applied small mini mold package.

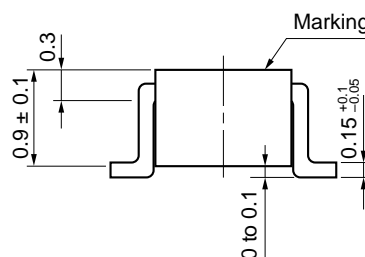
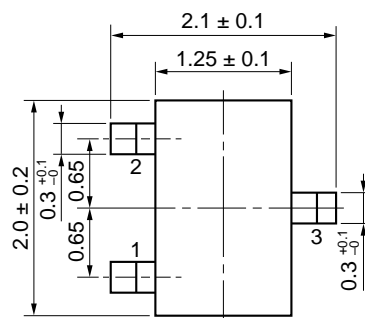
**FEATURES**

- Low Noise  
NF = 1.4 dB TYP. @  $f = 1$  GHz,  $V_{CE} = 3$  V,  $I_C = 7$  mA
- High Gain  
 $|S_{21e}|^2 = 12$  dB TYP. @  $f = 1$  GHz,  $V_{CE} = 3$  V,  $I_C = 7$  mA
- Small Mini Mold Package  
EIAJ: SC-70

**ORDERING INFORMATION**

PART NUMBER	QUANTITY	PACKING STYLE
2SC4227-T1	3 Kpcs/Reel.	Embossed tape 8 mm wide. Pin3 (Collector) face to perforation side of the tape.
2SC4227-T2	3 Kpcs/Reel.	Embossed tape 8 mm wide. Pin1 (Emitter), Pin2 (Base) face to perforation side of the tape.

\* Please contact with responsible NEC person, if you require evaluation sample. Unit sample quantity shall be 50 pcs. (Part No.: 2SC4227)

**PACKAGE DIMENSIONS**  
in millimeters**PIN CONNECTIONS**

1. Emitter
2. Base
3. Collector

**ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub> = 25 °C)**

Collector to Base Voltage	V <sub>CBO</sub>	20	V
Collector to Emitter Voltage	V <sub>CEO</sub>	10	V
Emitter to Base Voltage	V <sub>EBO</sub>	1.5	V
Collector Current	I <sub>C</sub>	65	mA
Total Power Dissipation	P <sub>T</sub>	150	mW
Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	−65 to +150	°C

**ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C)**

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
Collector Cutoff Current	I <sub>CBO</sub>			0.8	μA	V <sub>CB</sub> = 10 V, I <sub>E</sub> = 0
Emitter Cutoff Current	I <sub>EBO</sub>			0.8	μA	V <sub>EB</sub> = 1 V, I <sub>C</sub> = 0
DC Current Gain	h <sub>FE</sub>	40		240		V <sub>CE</sub> = 3 V, I <sub>C</sub> = 7 mA* <sup>1</sup>
Gain Bandwidth Product	f <sub>T</sub>	4.5	7.0		GHz	V <sub>CE</sub> = 3 V, I <sub>C</sub> = 7 mA
Feedback Capacitance	C <sub>re</sub>		0.45	0.9	pF	V <sub>CE</sub> = 3 V, I <sub>E</sub> = 0, f = 1 MHz* <sup>2</sup>
Insertion Power Gain	S <sub>21e</sub>   <sup>2</sup>	10	12		dB	V <sub>CE</sub> = 3 V, I <sub>C</sub> = 7 mA, f = 1 GHz
Noise Figure	NF		1.4	2.7	dB	V <sub>CE</sub> = 3 V, I <sub>C</sub> = 7 mA, f = 1 GHz

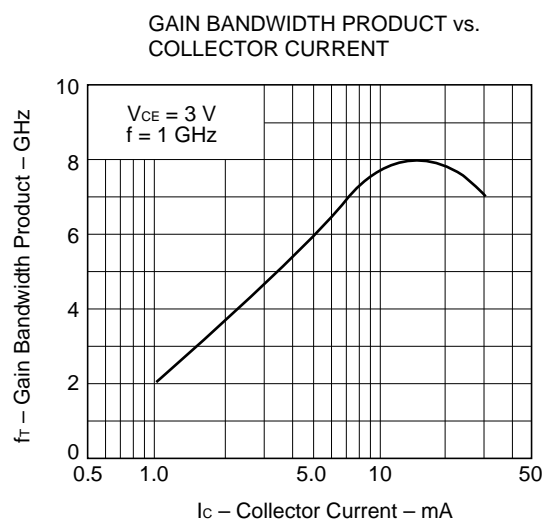
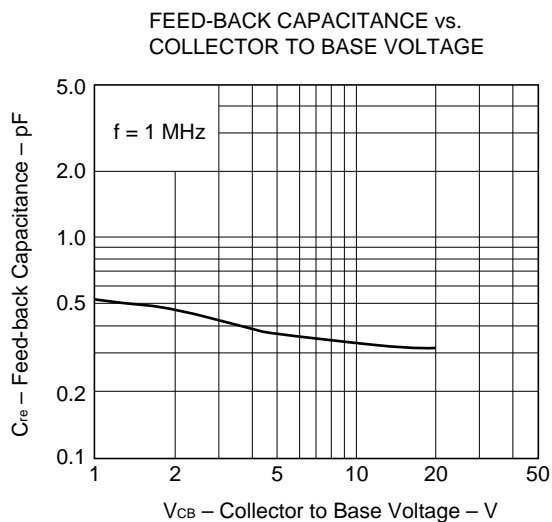
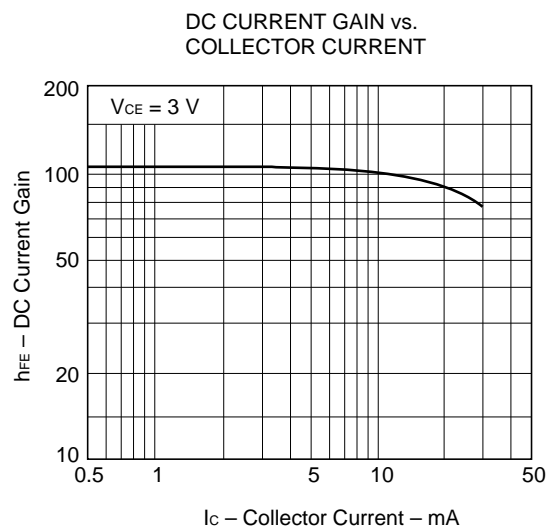
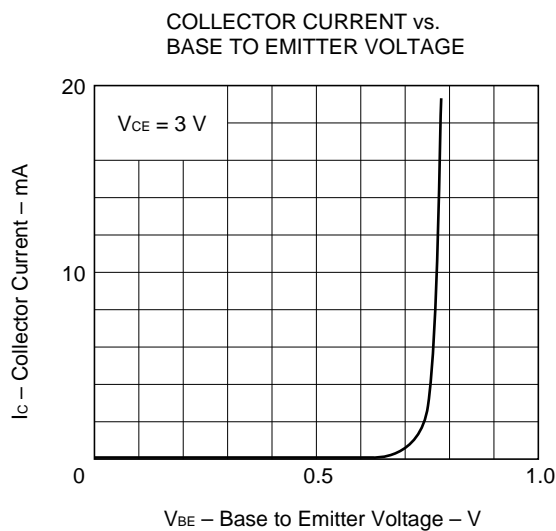
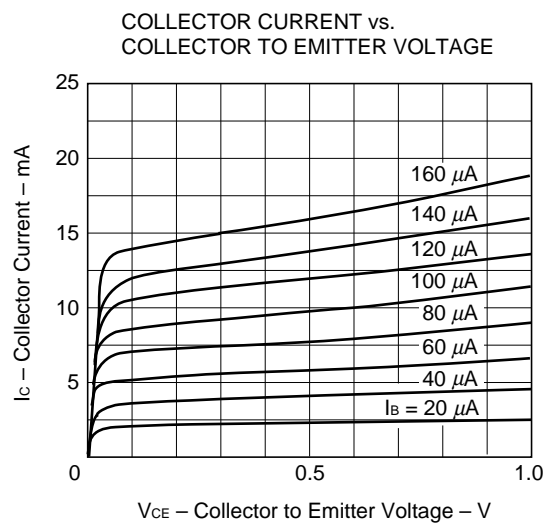
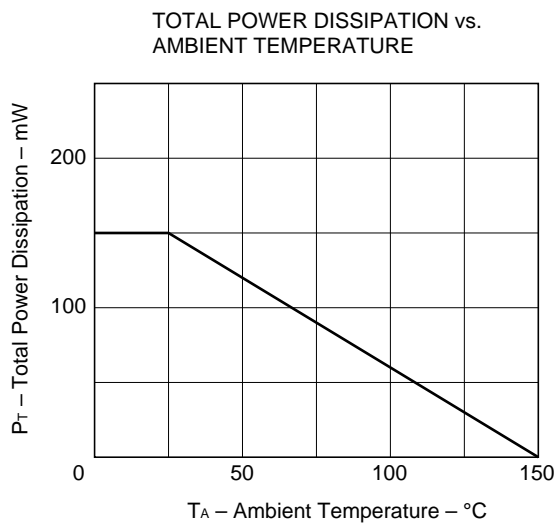
\*1 Pulse Measurement ; PW ≤ 350 μs, Duty Cycle ≤ 2 % Pulsed.

\*2 Measured with 3 terminals bridge, Emitter and Case should be grounded.

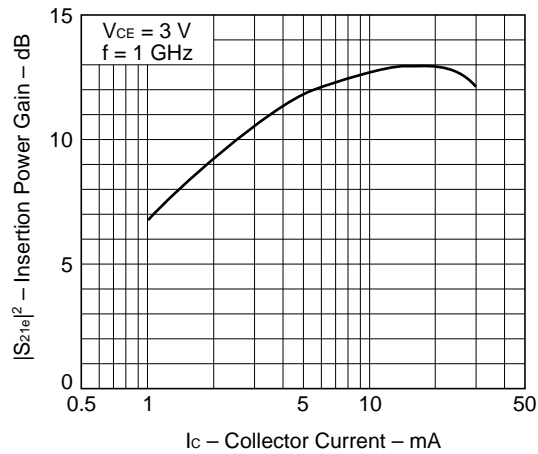
**h<sub>FE</sub> Classification**

Rank	R33	R34	R35
Marking	R33	R34	R35
h <sub>FE</sub>	40 to 90	70 to 150	110 to 240

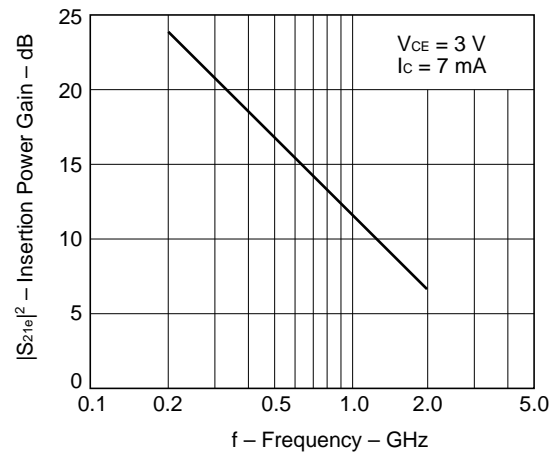
TYPICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ )



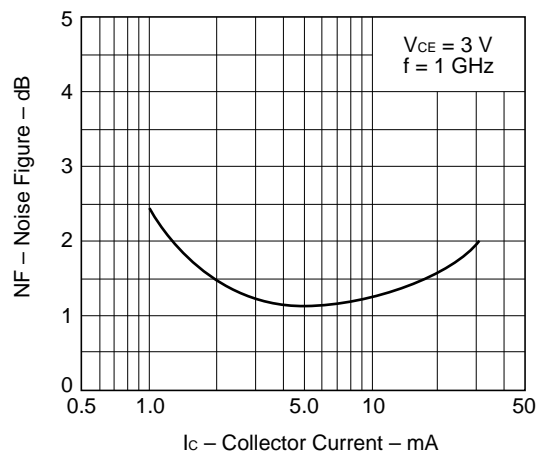
INSERTION POWER GAIN vs.  
COLLECTOR CURRENT



INSERTION POWER GAIN vs.  
FREQUENCY



NOISE FIGURE vs.  
COLLECTOR CURRENT



**S-PARAMETER**(V<sub>CE</sub> = 3 V, I<sub>C</sub> = 7 mA, Z<sub>O</sub> = 50 Ω)

FREQUENCY		S11		S21		S12		S22	
MHz	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG	
100.00	.804	−23.8	11.631	154.8	.023	74.8	.920	−16.5	
200.00	.692	−48.6	10.839	137.5	.040	64.1	.791	−27.7	
300.00	.581	−70.3	9.722	123.8	.050	59.9	.675	−33.5	
400.00	.489	−89.0	8.519	112.9	.060	56.7	.597	−37.0	
500.00	.419	−104.9	7.434	104.1	.067	55.9	.538	−38.7	
600.00	.376	−117.1	6.468	97.5	.075	55.6	.497	−40.0	
700.00	.342	−128.6	5.729	91.8	.082	55.7	.467	−41.0	
800.00	.321	−138.4	5.115	86.7	.089	56.3	.443	−41.7	
900.00	.305	−147.3	4.630	82.5	.096	56.1	.427	−42.5	
1000.00	.296	−155.2	4.207	78.5	.104	56.4	.412	−43.6	
1100.00	.289	−162.2	3.879	74.8	.111	56.0	.401	−44.6	
1200.00	.284	−169.3	3.595	71.4	.119	56.4	.393	−45.8	
1300.00	.282	−175.3	3.349	68.1	.127	56.2	.384	−47.3	
1400.00	.281	179.0	3.133	64.8	.136	56.0	.379	−48.8	
1500.00	.283	173.8	2.945	61.9	.143	55.4	.372	−50.1	
1600.00	.283	168.6	2.780	58.8	.151	55.0	.367	−51.8	
1700.00	.285	163.8	2.631	56.2	.160	54.4	.363	−53.7	
1800.00	.286	159.9	2.514	53.3	.168	53.9	.359	−55.4	
1900.00	.289	155.4	2.390	50.5	.177	53.3	.354	−57.3	
2000.00	.293	151.8	2.293	47.8	.186	52.5	.351	−59.2	

(V<sub>CE</sub> = 3 V, I<sub>C</sub> = 5 mA, Z<sub>O</sub> = 50 Ω)

FREQUENCY		S11		S21		S12		S22	
MHz	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG	
100.00	.818	−29.4	14.580	156.2	.023	79.9	.932	−14.4	
200.00	.689	−54.3	12.120	137.5	.040	65.1	.824	−23.4	
300.00	.594	−73.1	10.142	124.6	.052	55.0	.716	−30.3	
400.00	.500	−89.8	8.340	114.4	.063	58.5	.620	−32.2	
500.00	.457	−102.8	7.300	107.5	.069	56.4	.577	−34.2	
600.00	.404	−115.0	6.211	101.0	.081	54.9	.525	−35.1	
700.00	.377	−124.4	5.496	96.8	.084	59.5	.511	−36.1	
800.00	.359	−134.3	4.908	91.4	.091	58.4	.471	−36.2	
900.00	.342	−141.5	4.450	88.1	.097	58.4	.458	−35.3	
1000.00	.335	−150.3	4.018	84.7	.100	61.2	.440	−36.5	
1100.00	.326	−155.9	3.750	81.4	.112	61.8	.442	−36.8	
1200.00	.321	−162.4	3.410	78.1	.115	61.4	.417	−37.8	
1300.00	.317	−167.2	3.181	75.6	.124	62.3	.412	−38.5	
1400.00	.321	−173.4	2.995	72.5	.131	63.9	.411	−39.9	
1500.00	.318	−177.5	2.802	69.8	.138	63.6	.407	−40.4	
1600.00	.320	176.6	2.665	67.3	.149	66.4	.400	−41.1	
1700.00	.323	173.2	2.533	66.1	.156	65.3	.394	−43.7	
1800.00	.326	167.8	2.369	63.0	.162	65.9	.394	−44.3	
1900.00	.331	165.6	2.275	61.0	.177	65.4	.390	−45.5	
2000.00	.333	161.4	2.196	59.2	.183	64.5	.384	−47.6	

**S-PARAMETER**(V<sub>CE</sub> = 3 V, I<sub>C</sub> = 3 mA, Z<sub>0</sub> = 50 Ω)

FREQUENCY		S11		S21		S12		S22	
MHz		MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
100.00		.906	-22.7	9.710	161.6	.026	82.5	.962	-10.6
200.00		.810	-43.7	8.541	145.3	.049	63.8	.895	-18.3
300.00		.742	-60.6	7.695	133.4	.062	58.7	.811	-25.8
400.00		.638	-76.6	6.580	122.4	.073	56.0	.732	-27.7
500.00		.587	-89.8	5.934	114.1	.082	53.4	.680	-31.2
600.00		.524	-102.2	5.148	107.1	.091	49.7	.624	-33.5
700.00		.490	-111.4	4.627	102.2	.094	51.8	.603	-34.4
800.00		.460	-121.4	4.181	96.0	.099	51.2	.568	-35.0
900.00		.435	-129.9	3.827	92.6	.101	52.9	.540	-35.7
1000.00		.427	-138.2	3.443	88.1	.107	50.9	.523	-36.7
1100.00		.404	-144.9	3.199	84.2	.115	53.7	.512	-36.8
1200.00		.399	-151.7	2.989	79.8	.113	56.6	.500	-38.6
1300.00		.392	-157.9	2.779	77.4	.121	54.9	.489	-39.2
1400.00		.392	-163.6	2.638	73.5	.126	56.4	.483	-40.4
1500.00		.386	-169.1	2.443	71.3	.135	56.4	.477	-41.8
1600.00		.380	-174.5	2.344	68.0	.137	60.0	.477	-42.4
1700.00		.382	-179.7	2.239	65.3	.143	59.5	.466	-44.4
1800.00		.389	176.1	2.113	63.0	.151	59.4	.461	-44.9
1900.00		.383	172.5	2.025	61.4	.154	62.6	.456	-46.9
2000.00		.387	168.3	1.922	58.2	.163	62.0	.464	-48.3

(V<sub>CE</sub> = 3 V, I<sub>C</sub> = 7 mA, Z<sub>0</sub> = 50 Ω)

FREQUENCY		S11		S21		S12		S22	
MHz		MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
100.00		1.009	-14.5	3.544	168.8	.027	78.6	.994	-5.6
200.00		.955	-29.7	3.359	156.3	.055	73.6	.969	-10.1
300.00		.937	-42.6	3.277	147.1	.073	63.4	.947	-15.9
400.00		.864	-56.2	3.034	136.6	.091	57.7	.898	-18.8
500.00		.838	-67.3	2.891	128.6	.107	51.1	.865	-22.1
600.00		.775	-79.3	2.674	120.0	.116	46.6	.824	-25.8
700.00		.745	-88.5	2.485	114.2	.125	45.2	.803	-27.5
800.00		.708	-99.1	2.338	106.8	.127	41.2	.776	-29.7
900.00		.670	-107.9	2.177	101.4	.132	40.2	.740	-31.5
1000.00		.649	-116.8	2.052	96.0	.135	37.2	.723	-33.7
1100.00		.621	-124.0	1.914	90.8	.131	36.6	.719	-34.2
1200.00		.608	-131.8	1.819	86.0	.129	35.4	.700	-36.3
1300.00		.587	-138.5	1.713	82.4	.130	35.2	.691	-37.6
1400.00		.587	-144.5	1.628	77.7	.128	36.1	.681	-39.2
1500.00		.573	-152.6	1.533	73.4	.127	36.0	.662	-40.7
1600.00		.559	-157.1	1.464	70.3	.124	37.5	.660	-42.7
1700.00		.562	-164.2	1.421	67.2	.120	39.1	.658	-44.0
1800.00		.557	-168.9	1.350	64.7	.122	43.3	.658	-46.0
1900.00		.557	-173.9	1.296	61.1	.122	45.2	.641	-47.8
2000.00		.551	-178.6	1.240	58.0	.124	48.5	.643	-50.1

[MEMO]

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